JOURNALOF

Ceramic Processing Research

The effect of manganese doping on the grain size and transition temperature of barium titanate ceramics

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The structural and electrical properties of pure and manganese doped barium titanate (BaTiO₃) with a general formula $BaMn_xTi_{1-x}O_3$ (where x=0.00, 0.01, 0.02, 0.03, and 0.04) were investigated. For the observation of the surface morphology and estimation of grain sizes scanning electron microscopy (SEM) was employed. The grain size of $BaTiO_3$ increased with an increase of the Mn doping. The Curie temperature (T_c) which indicates the tetragonal-to-cubic transition, of each sample was found from the resistivity versus temperature curve, and T_c of $BaTiO_3$ increased linearly with an increase of the Mn doping. The T_c of un-doped $BaTiO_3$ was lower than that of the doped samples. The T_c value of pure $BaTiO_3$ was found to be 120 °C. It was found that the dielectric constant versus temperature curve also shows a similar type of T_c. The dielectric constant of $BaMn_xTi_{1-x}O_3$ was found to decrease with an increase of Mn doping and the T_c of $BaTiO_3$ increases with the addition of Mn.

Key words: Surface morphology, Grain size, Transition temperature, DC resistivity, Dielectric constant.

Introduction

Ferroelectricity is a phenomenon discovered in 1921 and a high dielectric constant was first discovered in the United States in 1942 [1-4]. In 1946 it was discovered that barium titanate (BaTiO₃) had a dielectric constant 100 times larger than that of other insulators [5]. It allows the manufacture of capacitors, which are smaller in size but have a larger capacity than other materials, thus improving electronic circuits and developing a new use for ceramic materials. The BaTiO₃ perovskite family includes many titanates used in various electroceramic applications, for examples, in electronics, in electrooptical devices, and in the electromechanical applications of ceramics. BaTiO₃ based compounds are commonly and frequently used in the electrical and electronic industries for their unique dielectric, ferroelectric and piezoelectric properties. In addition, because of its simple crystal structure, BaTiO₃ can easily form solid solutions with other oxides. For this reason BaTiO₃ is most widely used in various fields of electrical applications and widely utilized to manufacture electronic components such as multilayer capacitors (MLCs), positive temperature coefficient (PTC) thermistors, piezoelectric transducers, and a variety of electro-optic devices [6]. The high dielectric constant of BaTiO₃ makes it an especially desirable material as its electrical properties can be controlled within a wide

range by means of mixed crystal formation and doping. Because of the demand people, research on the dielectric (essentially non-conducting) characteristics of ceramic materials is increasing rapidly. At the same time people are attempting to reduce the size of all communication devices to be as small and as light as possible. Due to this trend, high dielectric constant materials such as barium titanate have become more and more important ceramics materials. BaTiO₃ powder is usually mixed with various types of additives in order to obtain a better performances and a good control over the grain size and electrical characteristics of the ceramic. It has been found that the dielectric properties of polycrystalline BaTiO₃ depend to a great extent on the grain growth during sintering and on the additive type and concentration [7, 8]. Additives which change the microstructure can also modify the dielectric properties of BaTiO₃ ceramics. Studies on the effect of a MnO₂ addition to BaTiO₃ found that a Mn addition shifted the Curie point and depressed the dielectric peak. Mn4+ can substitute for Ti⁴⁺ ions as an isovalent dopant. Addition of manganese particles into barium titanate can also form a core-shell structure. The desired temperature-stability in dielectric properties is achieved by the formation of core-shell grains [9]. In this study, the effects of MnO₂ doping on the microstructural development, electrical and dielectric properties of BaTiO₃ ceramics have been investigated.

Experimental Procedure

Barium carbonate (BaCO₃), titanium Dioxide (TiO₂) and manganese dioxide (MnO₂) were used for the

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Fig. 1. SEM images of $Ba(Mn_xTi_{1-x})O_3$ samples sintered at 1200 °C (a) x=0.0, (b) x=0.01, (c) x=0.02, (d) x=0.03, and (e) x=0.04.

preparation of [Ba(Mn_xTi_{1-x})O₃] samples (where x=0.00, 0.01, 0.02, 0.03 and 0.04) and the raw oxides were collected from the local market. The samples were prepared by a solid state reaction method where BaCO₃ and TiO₂ were used as the parent materials and MnO₂ was used as an additive. An appropriate amount of the starting materials was thoroughly mixed, dried and ball milled in a polyethylene jar for 12 hours in a wet medium and then calcined at 900 °C for one hour. The calcined powders were re-milled for 12 hours and pellets were formed by manually pressurizing the mixture. The pellets were then sintered at 1200 °C for four hours. A Hitachi S-3400N scanning electron microscope (SEM) was employed for the observation of the surface morphology and an estimation of grain sizes with increasing MnO2 content. These pellets were used for the measurement of the temperature-dependent resistivity and dielectric constant. For the electrical measurements both sides of the samples were coated with highly-conducting silver paste (Demetron, Leipzigerstr. 10, Germany) after polishing. A two-probe method was used for the measurement of the resistance and capacitance of the samples.

Results and Discussion

Surface morphology

The effects of MnO₂ additions to BaTiO₃ are



Fig. 2. Plot of resistivity versus temperature for the samples.

compared in the SEM micrographs shown in Fig. 1. The microstructure of $BaTiO_3$ ceramics doped with MnO_2 at different concentrations exhibits homogeneous grain distributions. A dense microstructure with smaller grains (average grain size~340.4 nm) was observed for pure $BaTiO_3$. The grain size increased linearly with an increase of MnO_2 doping in $BaTiO_3$.

Sample composition	Average Grain size, D (nm)	Resistivity at room temperature (Ω-cm)	Transitiontemperature, T _c (°C)	Resistivity at T _c (Ω-cm)
Ba(Mn _{0.00} Ti _{1.00})O ₃	340.40	16.8×10^{6}	120	36.6×10 ⁶
Ba(Mn _{0.01} Ti _{0.99})O ₃	415.37	14.5×10^{6}	130	21.9×10^{6}
Ba(Mn _{0.02} Ti _{0.98})O ₃	456.87	20.210^{6}	135	21.9×10^{6}
Ba(Mn _{0.03} Ti _{0.97})O ₃	526.00	16.3×10^{6}	145	20.4×10^{6}
Ba(Mn _{0.04} Ti _{0.96})O ₃	552.00	20.2×10^{6}	140	20.2×10^{6}

Table 1. Effect of Mn doping on different parameter of BaTiO₃



Fig. 3. Change of transition temperature (T_c) and grain size (D) due to Mn doping in BaMn_xTi_{1-x}O₃.

Temperature dependence of electrical resistivity

The effect of appropriate MnO_2 on the electrical behavior of doped BaTiO₃ can be analyzed through resistivity versus temperature curves as shown in Fig. 2. The direct current (DC) resistivity of BaTiO₃ was measured as a function of temperature and showed that the resistivity increased with temperature up to 120 °C and then decreased. This indicates a transition from tetragonal to cubic in the BaTiO₃ structure [10, 11]. The resistivity of BaTiO₃ at this transition temperature was found to be about $36.6 \times 10^6 \Omega$ -cm. The resistivities of the samples of MnO₂ doped BaMn_xTi_{1-x}O₃ show the same characteristics but the value of resistivity decreases with an increase of the doping concentration which is represented in Table 1. The transition temperature increases linearly with an increase in Mn doping in BaMn_xTi_{1-x}O₃ as shown in Fig. 3.

In Fig. 2 the resistivity showed an increase up to the transition temperature (tetragonal to cubic transition), passed through a maximum value and began to decrease. The resistivity showed a maximum value of about $36.6 \times 10^6 \Omega$ -cm when the sample was pure and the grain size was around 340.4 nm. With Mn doping in the first step the resistivity decreases significantly but with further doping, the resistivity decreases



Fig. 4. Dielectric Constant as a function temperature of $Ba(Mn_xTi_{1-x})O_3$ samples.

slowly. As the resistivity of BaTiO₃ strongly depends on the grain size, so with an increase of the grain size of the samples the resistivity decreases and the T_c increases with an increase of the grain size as shown in Fig. 3. It is observed that BaTiO₃ has the lowest transition temperature, while when Mn is added to BaMn_xTi_{1-x}O₃, the T_c increased and the highest transition was found to be 145 °C for x=0.03. In contrast, with an increase of the value of x in BaMn_xTi_{1-x}O₃ at x=0.04 the T_c decreased to 140 °C as listed in Table 1. The shift of the transition temperature for x=0.04 may be due to some structural disorder.

Temperature dependence of dielectric constant

The observed microstructural features together with the type of additive have a direct influence on the dielectric properties of doped BaTiO₃. Figure 4 shows the variation of the dielectric constant of the compounds with temperature for different concentrations of Mn in BaMn_xTi_{1-x}O₃. It was found to follow the general trend of ferroelectrics i.e., the dielectric constant increases with a rise in temperature up to a maximum value at the Curie temperature (T_c) where it undergoes a phase transition from a ferroelectric to a para-electric phase. It is observed in Fig. 4 that for un-doped BaTiO₂, the

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Sample composition	Average Grain size (nm)	Transition temperature, T _c (°C)	Dielectric Constant, ϵ at T_{c}
Ba(Mn _{0.00} Ti _{1.00})O ₃	340.40	125	646.11
$Ba(Mn_{0.01}Ti_{0.99})O_3$	415.37	150	552.96
$Ba(Mn_{0.02}Ti_{0.98})O_3$	456.87	155	534.13
Ba(Mn _{0.03} Ti _{0.97})O ₃	526.00	160	530.97
Ba(Mn _{0.04} Ti _{0.96})O ₃	552.00	160	528.04

Table 2. Change in dielectric constant, e at T_c.

dielectric constant reaches a maximum value of about 646 at temperature 125 °C and above this temperature it decreases. Dielectric properties have been found to be dependent on the grain size [12,13]. With an increase of MnO_2 the dielectric constant of the samples at T_c decreases to a value of about 528 for sample 5. Thus it is seen that the grain size increases as the MnO_2 content increases in BaTiO₃ thereby decreasing the dielectric constant at the T_c as shown in Table 2.

It was found that when Mn was doped the transition temperature of $BaMn_xTi_{1-x}O_3$ increases with an increase of the value of x as well as grain size. When the grain size was about 415 nm, the transition temperature increased rapidly and then increased slowly with an increase of the grain size.

Conclusions

The DC electrical resistivity, dielectric and microstructural properties of BaTiO₃ ceramics was influenced significantly by small additions of MnO_2 . It is found that with an increase of Mn in BaMn_xTi_{1-x}O₃ (where x=0.00, 0.01, 0.02, 0.03 and 0.04), the grain size of the samples increases. The un-doped BaTiO₃ sample exhibited the highest resistivity among the experimental samples. This increases with temperature up to a maximum value at a temperature which is termed the Curie temperature or the transition temperature (T_c) and then the resistivity decreases. The T_c rises with an increase of the value of x in BaMn_xTi_{1-x}O₃ as well as the grain size. The dielectric constant of the pure BaTiO₃ sample was largest and was found to decrease with an increase of the grain size.

Acknowledgments

The authors acknowledge to Bangladesh Council of Scientific and Industrial Research, Dhaka-1205, Bangladesh for the financial help in the research work.

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